

## PATENT ASSIGNMENT COVER SHEET

Electronic Version v1.1  
 Stylesheet Version v1.2

EPAS ID: PAT7547487

SUBMISSION TYPE:	NEW ASSIGNMENT
NATURE OF CONVEYANCE:	ASSIGNMENT

## CONVEYING PARTY DATA

Name	Execution Date
DOW SILICONES CORPORATION	08/27/2019

## RECEIVING PARTY DATA

Name:	DDP SPECIALTY ELECTRONIC MATERIALS US 9, LLC
Street Address:	974 CENTER ROAD
City:	WILMINGTON
State/Country:	DELAWARE
Postal Code:	19805

## PROPERTY NUMBERS Total: 3

Property Type	Number
Application Number:	16755043
Application Number:	16755048
Application Number:	16755049

## CORRESPONDENCE DATA

## Fax Number:

*Correspondence will be sent to the e-mail address first; if that is unsuccessful, it will be sent using a fax number, if provided; if that is unsuccessful, it will be sent via US Mail.*

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 JYANDO@sternekessler.com, TARJAHN@sternekessler.com,

Correspondent Name: STERNE, KESSLER, GOLDSTEIN & FOX P.L.L.C.

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ATTORNEY DOCKET NUMBER: 5096.001-2,002-2,003-2

NAME OF SUBMITTER: MATTHEW S. BODENSTEIN

SIGNATURE: /Matthew S. Bodenstein/

DATE SIGNED: 09/20/2022

## Total Attachments: 27

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## FORM OF PATENT ASSIGNMENT

This PATENT ASSIGNMENT (this “Assignment”), dated as of November 1, 2018 (the “Effective Date”), is by and between Dow Silicones Corporation (f/k/a Dow Corning Corporation), a Michigan corporation (“Assignor”) and DDP Specialty Electronic Materials US 9, LLC, a Delaware limited liability company (“Assignee”), (each a “Party” and collectively, the “Parties”).

**WHEREAS**, Assignor owns the issued patents and patent applications set forth on Schedule A hereto (the foregoing, including all patents issuing from any patent applications, collectively, the “Assigned Patents”); and

**WHEREAS**, the Parties hereto agree that the Assignor contribute, transfer, assign and convey to the Assignee all of its right, title and interest in and to the Assigned Patents and that the Assignee accept such contribution, transfer, assignment and conveyance of such Assigned Patents;

**NOW, THEREFORE**, in consideration of the foregoing and the covenants and agreements contained in this Assignment, the receipt and sufficiency of which are hereby acknowledged, the Parties hereby agree as follows:

1. **Conveyance**. Assignor hereby assigns, transfers and conveys to Assignee all of Assignor’s right, title and interest in and to the Assigned Patents, together with any and all (a) related continuations, continuations-in-part, divisionals, reissues, reexaminations, substitutions, extensions, and foreign equivalents thereof and (b) priority rights derived from any the Assigned Patents, or the items described in the foregoing subsection (a), by virtue of the International Convention for the Protection of Industrial Property and any other rights provided under applicable treaties or conventions, including rights in any and all provisional applications, together with all rights and remedies against past, present, and future infringement, misappropriation, or other violation thereof, including the right to enforce the foregoing and to sue for and recover profits and damages for any and all infringements, misappropriations or violations thereof, whether past, present or future, to the full end of the term or terms for which said patents may be granted, as fully and entirely as the same would have been held and enjoyed by Assignor without this assignment (the rights transferred under this Section 1 cumulatively, the “Assigned Rights”).

2. **Recordation; Further Assurances**. Assignor and Assignee shall each take any and all additional actions as may be reasonably necessary to effect the transactions contemplated hereby, including Assignor’s execution of individual assignment documentation prepared by Assignee at Assignee’s expense for filing with the authorities of each individual country. In furtherance of the foregoing, Assignor agrees that with respect to the Assigned Patents it will enter into an assignment agreement suitable for filing with the authorities of each individual country (each an “Recordal Instrument”). The Parties agree that any Recordal Instrument shall give no greater rights or remedies in respect of the transaction completed in such Recordal

Instrument than those provided for herein and Section 4 of this Assignment shall apply to any Recordal Instrument as if fully set forth therein. As between the Parties, the responsibility to file assignments with the national patent offices of each country for the Assigned Patents shall be on the Assignee and the Assignee shall bear the cost of filing such assignments (unless, as of the Effective Date, the patent registration or application is not properly recorded in the name of the Assignor or an Affiliate of Assignor, in which case, at the request of Assignee, the Parties shall reasonably cooperate to make the necessary corrective filings and recordals of the documents that are available to them and shall split evenly any expenses in connection with the foregoing corrections and each Party shall provide any receipts and expense documentation to the other Party for the purposes of splitting such expenses).

3. Prosecution and Maintenance. For the avoidance of doubt but without limiting the obligations set forth in Section 2 hereof, as of and following the Effective Date, Assignor will have no responsibility to take any action to maintain any of the patents included in the Assigned Rights or further prosecute or seek issuance of any patent applications included in the Assigned Rights, including payment of fees, responses to any office action or other inquiries from agents of governmental entities or registrars, or otherwise.

4. No Claims. Except with respect to Section 2 of this Assignment, neither Party nor any of their respective affiliates or representatives will have, or be subject to, any liability or indemnification obligation under this Assignment to the other Party, any of its affiliates or representatives or any other entity or person resulting from, or in connection with, this Assignment or the transactions contemplated hereby. Except with respect to Section 2, each of the Parties hereby agrees (a) not to bring any claim or Action (as defined herein) under this Assignment against the other Party, its affiliates or representatives and (b) to cause its respective affiliates and representatives to comply with this Section 4. “Action” shall mean any claims, actions, suits, inquiries, proceedings or investigations by or before any governmental authority or arbitral tribunal.

5. Disclaimer of Representations and Warranties. ASSIGNEE (ON BEHALF OF ITSELF AND ITS AFFILIATES) UNDERSTANDS AND AGREES THAT NO PARTY TO THIS ASSIGNMENT IS REPRESENTING OR WARRANTING IN ANY WAY IN THIS ASSIGNMENT, AND HEREBY EXPRESSLY DISCLAIMS ALL REPRESENTATIONS AND WARRANTIES, AS TO THE ASSIGNED PATENTS AND THE OTHER ASSIGNED RIGHTS, AS TO ANY CONSENTS OR APPROVALS (INCLUDING APPROVALS FROM ANY GOVERNMENTAL ENTITIES) REQUIRED IN CONNECTION HEREWITH OR THEREWITH, AS TO THE VALUE OR FREEDOM FROM ANY SECURITY INTERESTS OF OR THE NON-INFRINGEMENT OR ABSENCE OF OTHER VIOLATION, VALIDITY OR ENFORCEABILITY OR ANY OTHER MATTER CONCERNING THE ASSIGNED PATENTS AND OTHER PATENTS AND PATENT APPLICATIONS INCLUDED IN THE ASSIGNED RIGHTS, AND ALL OF THE ASSIGNED PATENTS AND OTHER ASSIGNED RIGHTS ARE BEING TRANSFERRED ON AN “AS IS, WHERE IS” AND “WITH ALL FAULTS” BASIS.

6. Successors and Assigns. The provisions of this Assignment and the obligations and rights hereunder shall be binding upon, inure to the benefit of and be enforceable by (and against) the Parties and their respective successors and permitted transferees and assigns.

7. Counterparts. This Assignment may be executed in more than one counterpart, all of which shall be considered one and the same agreement, and shall become effective when one or more such counterparts have been signed by each of the Parties and delivered to each of the Parties.

8. Title and Headings. Titles and headings to sections herein are inserted for the convenience of reference only and are not intended to be a part of or to affect the meaning or interpretation of this Assignment.

9. Governing Law. This Assignment and any dispute arising out of, in connection with or relating to this Assignment shall be governed by and construed in accordance with the Laws of the State of Delaware, without giving effect to the conflicts of laws principles thereof.

*[Signature Page Follows]*

IN WITNESS WHEREOF, Assignor and Assignee have duly executed this Assignment as of the date first written above.

ASSIGNOR:

DOW SILICONES CORPORATION

By:   
Name: Jonathan P. Wendt  
Title: Secretary

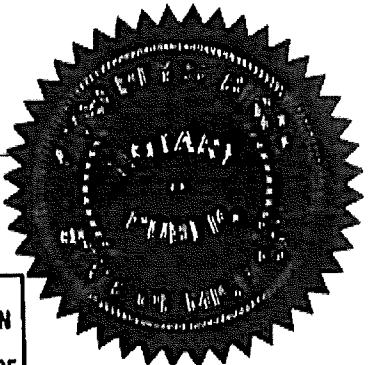
THE STATE OF MICHIGAN

County of Midland

This instrument was executed before me on this 23rd day of August, 2019, by Jonathan P. Wendt, the Secretary of Dow Silicones Corporation, a Michigan corporation, on behalf of said company.

  
Notary Public in and for  
The State of Michigan

KIMBERLY S. BIRCH  
NOTARY PUBLIC - STATE OF MICHIGAN  
COUNTY OF MIDLAND  
My Commission Expires March 16, 2025  
Acting in the County of MIDLAND



*Signature Page to Patent Assignment*

PATENT  
REEL: 061479 FRAME: 0083

Acknowledged and Accepted:

ASSIGNEE:

DDP SPECIALTY ELECTRONIC  
MATERIALS US 9, LLC

By: Calissa W. Brown

Name: Calissa W. Brown

Title: Assistant Secretary

THE STATE OF DELAWARE

County of New Castle

This instrument was executed before me on this 27<sup>th</sup> day of August, 2019, by  
Calissa W. Brown, the Assistant Secretary (title) of DDP Specialty  
Electronic Materials US 9, LLC, a Delaware limited liability company, on behalf of said  
company.



Mary Jane Ford  
Notary Public in and for  
The State of DELAWARE

MARY-JANE FORD  
Printed or Typed Name of Notary

My commission expires JAN. 4, 2023

*Signature Page to Patent Assignment*

PATENT  
REEL: 061479 FRAME: 0084

SCHEDULE A TO PATENT ASSIGNMENT

PATENT  
REEL: 061479 FRAME: 0085

**SCHEDULE A**  
PATENTS

CASE REFERENCE	REFERENCE COUNTRY	TITLE	OWNER	FILING DATE/APP. NUMBER	PUB. NUMBER	GRANT DATE	GRANT NUMBER
79673-TW-NP	Taiwan	THIO(DI)SILANES	DOW SILICONES CORPORATION	10/11/2017 106134800	201813972		
79673-TW-NP[2]	Taiwan	THIO(DI)SILANES	DOW SILICONES CORPORATION	10/12/2017 106134970	201813971		
79673-WO-PCT	International Procedure	THIO(DI)SILANES	DOW SILICONES CORPORATION	10/10/2017 PCT/US17/05587	WO/2018/071371		
79673-WO-PCT[2]	International Procedure	THIO(DI)SILANES HIGH PURITY TRISILYLAMINE, METHODS OF	DOW SILICONES CORPORATION	10/10/2017 PCT/US17/055874	WO/2018/071379		
79679-CN-PCT	China	MAKING, AND USE HIGH PURITY TRISILYLAMINE, METHODS OF	DOW SILICONES CORPORATION	12/16/2016 PCT/US16/067143			
79679-EP-EPT (Patents)	European Procedure	MAKING, AND USE HIGH PURITY TRISILYLAMINE, METHODS OF	DOW SILICONES CORPORATION	12/16/2016 16840347.5			
79679-JP-PCT	Japan	MAKING, AND USE HIGH PURITY TRISILYLAMINE, METHODS OF	DOW SILICONES CORPORATION	12/16/2016 2018-531566			
79679-KR-PCT	Korea	MAKING, AND USE HIGH PURITY TRISILYLAMINE, METHODS OF	DOW SILICONES CORPORATION				
79679-TW-NP	SOUTH KOREA	MAKING, AND USE HIGH PURITY TRISILYLAMINE, METHODS OF	DOW SILICONES CORPORATION	12/16/2016 10-2018-7019383			
79679-TW-NP	Taiwan	MAKING, AND USE HIGH PURITY TRISILYLAMINE,	DOW SILICONES CORPORATION	12/16/2016 105141895	201722849		
79679-US-PCT	United States Of America	METHODS OF MAKING, AND USE TRANSSILYLATION	DOW SILICONES CORPORATION	12/16/2016 16/061477			
79848-TW-NP	Taiwan	CATALYSIS	DOW SILICONES CORPORATION	12/01/2017 106142099	201823149		
79848-WO-PCT	International Procedure	TRANSSILYLATION CATALYSIS METHOD FOR MAKING AN ORGANOAMINOSILANE; A METHOD FOR MAKING A SILYLAMINE FROM THE	DOW SILICONES CORPORATION	11/29/2017 PCT/US17/063588	WO/2018/125476		
79930-CN-PCT	China	ORGANOAMINOSILANE; A METHOD FOR MAKING AN ORGANOAMINOSILANE; A METHOD FOR MAKING A SILYLAMINE FROM THE	DOW SILICONES CORPORATION	12/16/2016 PCT/US16/067152			
79930-EP-EPT (Patents)	European Procedure	ORGANOAMINOSILANE; A METHOD FOR MAKING AN ORGANOAMINOSILANE; A METHOD FOR MAKING A SILYLAMINE FROM THE	DOW SILICONES CORPORATION	12/16/2016 16840348.3			
79930-JP-PCT	Japan	ORGANOAMINOSILANE; A METHOD FOR MAKING AN ORGANOAMINOSILANE; A METHOD FOR MAKING A SILYLAMINE FROM THE	DOW SILICONES CORPORATION	12/16/2016 2018-531616			
79930-KR-PCT	SOUTH KOREA	ORGANOAMINOSILANE; A METHOD FOR	DOW SILICONES CORPORATION	12/16/2016 10-2018-7019018			

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METHOD FOR  
MAKING AN  
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NE; A METHOD FOR  
MAKING A  
SILYLAMINE FROM  
THE  
ORGANOAMINOSILA DOW SILICONES  
79930-TW-NP Taiwan NE CORPORATION 12/16/2016 105141899 201734024

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79930-US-	United States Of	METHOD FOR MAKING AN ORGANOAMINOSILA NE; A METHOD FOR MAKING A SILYLAMINE FROM THE ORGANOAMINOSILA DOW SILICONES		
PCT	America	NE	CORPORATION	12/16/2016 16/061461
80066-CN-PCT	China European	TRIS(DISILANYL)AM DOW SILICONES INE	CORPORATION	12/16/2016 PCT/US16/067075
80066-EP-EPT (Patents)	Procedure	TRIS(DISILANYL)AM DOW SILICONES INE	CORPORATION	12/16/2016 16822354.3
80066-JP-PCT	Japan	TRIS(DISILANYL)AM DOW SILICONES INE	CORPORATION	12/16/2016 2018-528601
80066-KR-PCT	SOUTH KOREA	TRIS(DISILANYL)AM DOW SILICONES INE	CORPORATION	12/16/2016 10-2018-7018305
80066-US-PCT	United States Of	TRIS(DISILANYL)AM DOW SILICONES INE	CORPORATION	12/16/2016 15/776851
80066-WO-PCT	International Procedure	TRIS(DISILANYL)AM DOW SILICONES INE	CORPORATION	12/16/2016 PCT/US16/067075 WO/2017/106587
80067-TW-NP	Taiwan	CATALYSIS OF DEHYDROCOUPLING REACTIONS BETWEEN AMINES AND SILANES	DOW SILICONES CORPORATION	12/18/2017 106144433 201823255
80067-WO-PCT	International Procedure	DEHYDROCOUPLING REACTIONS BETWEEN AMINES AND SILANES	DOW SILICONES CORPORATION	11/29/2017 PCT/US17/063590 WO/2018/125477
80234-CN-NP	China	METHOD FOR FABRICATING SEMICONDUCTOR DEVICE	DOW SILICONES CORPORATION	01/24/2018 201810069059.4
80234-JP-NP	Japan	METHOD FOR FABRICATING SEMICONDUCTOR DEVICE	DOW SILICONES CORPORATION	01/24/2018 2018-9515
80234-KR-NP	SOUTH KOREA	METHOD FOR FABRICATING SEMICONDUCTOR DEVICE	DOW SILICONES CORPORATION	02/09/2017 10-2017-0017908
80234-TW-NP	Taiwan	FABRICATING SEMICONDUCTOR DEVICE	DOW SILICONES CORPORATION	12/27/2017 106146025
80234-US-NP	United States Of	METHOD FOR FABRICATING SEMICONDUCTOR DEVICE	DOW SILICONES CORPORATION	01/25/2017 15/414913 08/14/2018 10049882
80416-TW-NP	Taiwan	MAKING A HALOSILOXANE METHOD OF	DOW SILICONES CORPORATION	05/31/2018 107118812
80416-WO-PCT	International Procedure	MAKING A HALOSILOXANE METHOD OF	DOW SILICONES CORPORATION	05/24/2018 PCT/US18/034344
80769-TW-NP	Taiwan	MAKING HALOSILOXANE METHOD OF	DOW SILICONES CORPORATION	06/01/2018 107119060
80769-WO-PCT	International Procedure	MAKING HALOSILOXANE	DOW SILICONES CORPORATION	05/24/2018 PCT/US18/034402
80813-EP-EPA (Patents)	European Procedure	A METHOD OF CLEANSING SKIN USING A TWO-PART, HYDROSILYLATION CURABLE SILICONE COMPOSITION METHOD FOR PRODUCING LED BY	DOW SILICONES CORPORATION	03/28/2018 18305348.7
80860-WO-PCT	International Procedure	ONE STEP FILM LAMINATION SILICONE COMPOSITIONS AND ARTICLES FOR CONTROLLING LIGHT SILICONE COMPOSITIONS AND	DOW SILICONES CORPORATION	05/18/2018 PCT/CN18/087460
80870-TW-NP	Taiwan	CONTROLLING LIGHT SILICONE COMPOSITIONS AND	DOW SILICONES CORPORATION	07/10/2018 107123796

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80870-WO-  
PCT International  
Procedure

ARTICLES FOR  
CONTROLLING  
LIGHT

DOW SILICONES  
CORPORATION

07/13/2018 PCT/US18/041960

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80872-TW-NP Taiwan		CURED SILICONE COMPOSITION FOR DOW SILICONES LED ENCAPSULANTS CORPORATION ANTIFRICTION COATING (AFC) COMPOSITION AND	DOW SILICONES CORPORATION	07/06/2018 62/694496
80886-US-PSP[2]	United States Of America	AFC FORMED THEREFROM	DOW SILICONES CORPORATION	07/06/2018 62/694496
80891-TW-NP Taiwan		METHOD OF PREPARING PENTACHLORODISIL ANE AND PURIFIED REACTION PRODUCT DOW SILICONES COMPRISING SAME CORPORATION		07/04/2018 107123211
80891-WO-PCT	International Procedure	METHOD OF PREPARING PENTACHLORODISIL ANE AND PURIFIED REACTION PRODUCT DOW SILICONES COMPRISING SAME CORPORATION		07/30/2018 PCT/US18/44390
80892-TW-NP Taiwan		1,1,1- TRIS(DIMETHYLAMI NO)DISILANE AND METHOD OF PREPARING SAME DOW SILICONES 1,1,1- TRIS(DIMETHYLAMI NO)DISILANE AND	CORPORATION	07/04/2018 107123212
80892-WO-PCT	International Procedure	METHOD OF PREPARING SAME DOW SILICONES SYNTHESIS 1,1,1- TRICHLORODISILAN DOW SILICONES	CORPORATION	07/30/2018 PCT/US18/44392
80901-TW-NP Taiwan		E SYNTHESIS 1,1,1- TRICHLORODISILAN DOW SILICONES	CORPORATION	06/27/2018 107122060
80901-WO-PCT	International Procedure	E METHOD OF MAKING A MIXTURE OF FAR BOILING SILANE AND	CORPORATION	06/21/2018 PCT/US18/038711
80972-TW-NP Taiwan		SILOXANE METHOD OF MAKING A MIXTURE OF FAR BOILING	DOW SILICONES CORPORATION	07/25/2018 107125633
80972-WO-PCT	International Procedure	SILANE AND SILOXANE LUBRICATING	DOW SILICONES CORPORATION	06/22/2018 PCT/US18/039010
81138-US-PSP America	United States Of America	GREASE COMPOSITION	DOW SILICONES CORPORATION	12/21/2017 62/608595
81485-WO-PCT	International Procedure	CONTROL OF ADHESIVE DOMAINS	DOW SILICONES CORPORATION	07/19/2017 PCT/EP17/068212 WO 2018/015424
81496-TW-NP Taiwan		HYDROSILYLATION- CURABLE SILICONE DOW SILICONES COMPOSITION	CORPORATION	
81496-US-PSP America	United States Of America	HYDROSILYLATION- CURABLE SILICONE DOW SILICONES COMPOSITION	CORPORATION	11/16/2017 62/587235
81496-WO-PCT	International Procedure	HYDROSILYLATION- CURABLE SILICONE DOW SILICONES COMPOSITION	CORPORATION	
81556-US-PSP America	United States Of America	HYDROCARBOXY DOW SILICONES DISILANES	CORPORATION	12/08/2017 62/596202
81682-US-PSP America	United States Of America	LUBRICANT COMPOSITIONS	DOW SILICONES CORPORATION	07/18/2018 62/699777
81710-EP-EPA (Patents)	European Procedure	TRANSDERMAL THERAPEUTIC SYSTEM FOR THE TRANSDERMAL ADMINISTRATION OF GUANFACINE COMPRISING AT LEAST ONE ADDITIVE	DOW SILICONES CORPORATION	12/05/2017 17205546.9

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		TRANSDERMAL THERAPEUTIC SYSTEM FOR THE TRANSDERMAL ADMINISTRATION OF GUANFACINE COMPRISING AT	DOW SILICONES CORPORATION	10/11/2017 62/570745	
81710-US-PSP	United States Of America	LEAST ONE ADDITIVE			
		TRANSDERMAL THERAPEUTIC SYSTEM FOR THE TRANSDERMAL ADMINISTRATION OF GUANFACINE COMPRISING A	DOW SILICONES CORPORATION	12/05/2017 17205543.6	
81711-EP-EPA (Patents)	European Procedure	SILICONE POLYMER			
		TRANSDERMAL THERAPEUTIC SYSTEM FOR THE TRANSDERMAL ADMINISTRATION OF GUANFACINE COMPRISING A SILICONE POLYMER	DOW SILICONES CORPORATION	10/11/2017 62/570746	
81711-US-PSP	United States Of America	TRANSDERMAL THERAPEUTIC SYSTEM FOR THE TRANSDERMAL ADMINISTRATION OF GUANFACINE COMPRISING A SILICONE POLYMER			
81712-EP-EPA (Patents)	European Procedure	HYBRI POLYMER	DOW SILICONES CORPORATION	12/05/2017 17205538.6	
		TRANSDERMAL THERAPEUTIC SYSTEM FOR THE TRANSDERMAL ADMINISTRATION OF GUANFACINE COMPRISING A SILICONE ACRYLIC HYBRI POLYMER			
81712-US-PSP	United States Of America	SILICONE ACRYLIC HYBRI POLYMER COMPOSITION, COATING FILM USING THE SAME, SLIDING MEMBER HAVING THE COATING AND PROCESS FOR PRODUCING THE SAME	DOW SILICONES CORPORATION	10/11/2017 62/570748	
81806-JP-NP	Japan European Procedure			06/11/2018 2018-111105	
81841-EP-EPA (Patents)		THERMOPLASTIC COMPOSITION Silicone Skin Adhesive	DOW SILICONES CORPORATION	04/05/2018 18305403.0	
DC10044-DE-EPT	Germany	Gels With Enhanced Adhesion To Plastic Substrates Silicone Skin Adhesive	DOW SILICONES CORPORATION	03/18/2005 05726039.0	1737504 06/09/2010 602005021767.3
DC10044-FI-EPT	Finland	Gels With Enhanced Adhesion To Plastic Substrates Silicone Skin Adhesive	DOW SILICONES CORPORATION	03/18/2005 05726039.0	1737504 06/09/2010 1737504
DC10044-FR-EPT	France	Gels With Enhanced Adhesion To Plastic Substrates Silicone Skin Adhesive	DOW SILICONES CORPORATION	03/18/2005 05726039.0	1737504 06/09/2010 1737504
DC10044-GB-EPT	United Kingdom	Gels With Enhanced Adhesion To Plastic Substrates Silicone Skin Adhesive	DOW SILICONES CORPORATION	03/18/2005 05726039.0	1737504 06/09/2010 1737504
DC10044-JP-PCT	Japan	Gels With Enhanced Adhesion To Plastic Substrates Composition Comprising Neopentasilane And Method Of Preparing Same	DOW SILICONES CORPORATION	03/18/2005 2007-507334	2007-532179 10/28/2011 4849477
DC10119-CN-PCT	China			08/29/2007 200780039179.X	101528813 10/26/2011 200780039179.X

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DC10119-DE-EPT	Germany	Composition Comprising Neopentasilane And Method Of Preparing Same Composition Comprising	DOW SILICONES CORPORATION	08/29/2007 07811642.3	2076558	04/18/2018 602007054612.5
DC10119-EP-EPT (Patents)	European Procedure	Neopentasilane And Method Of Preparing Same Composition Comprising	DOW SILICONES CORPORATION	08/29/2007 07811642.3	2076558	04/18/2018 2076558
DC10119-JP-PCT	Japan	Method Of Preparing Same Composition Comprising Neopentasilane And	DOW SILICONES CORPORATION	08/29/2007 2009-534570	2010507559	10/05/2012 5103480
DC10119-KR-PCT	SOUTH KOREA	Method Of Preparing Same Composition Comprising Neopentasilane And	DOW SILICONES CORPORATION	08/29/2007 20097008553		03/20/2015 1506136
DC10119-TW-NP	Taiwan	Method Of Preparing Same Composition Comprising Neopentasilane And	DOW SILICONES CORPORATION	09/12/2007 096134053	200821322	10/21/2013 I412530
DC10119-US-PCT	United States Of America	Method Of Preparing Same Deposition Method Of Insulating Layers Having Low Dielectric Constant Of	DOW SILICONES CORPORATION	08/29/2007 12/440299	20100176338	04/03/2012 8147789
DC10165-CN-PCT	China	Semiconductor Device Deposition Method Of Insulating Layers Having Low Dielectric Constant Of	DOW SILICONES CORPORATION	07/16/2002 02828976.5	1625799	05/30/2007 1319125
DC10165-JP-PCT	Japan	Semiconductor Device Deposition Method Of Insulating Layers Having Low Dielectric Constant Of	DOW SILICONES CORPORATION	07/16/2002 2004-506072	2005-526397	05/13/2009 4262676
DC10165-KR-NP	SOUTH KOREA	Semiconductor Device Deposition Method Of Insulating Layers Having Low Dielectric Constant Of	DOW SILICONES CORPORATION	05/17/2002 2002-0027413	2003-0089267	01/06/2009 0878270
DC10165-US-NP	United States Of America	Constant Of Semiconductor Device	DOW SILICONES CORPORATION	05/17/2002 10/150480	20030215970	01/10/2006 6984594
DC10284-BE-ETD	Belgium	Fluid Transfer Assembly	DOW SILICONES CORPORATION	10/23/2006 11173988.4	2383502	11/20/2013 2383502
DC10284-BE-ETD[2]	Belgium	Fluid Transfer Assembly	DOW SILICONES CORPORATION	10/23/2006 11174007.2	2383503	05/29/2013 2383503
DC10284-CN-PCT	China	Fluid Transfer Assembly	DOW SILICONES CORPORATION	10/23/2006 200680043332.1	101313168	04/03/2013 200680043332.1
DC10284-DE-EPT	Germany	Fluid Transfer Assembly	DOW SILICONES CORPORATION	10/23/2006 06826606.3	1952052	08/27/2014 602006042876.6
DC10284-DE-ETD	Germany	Fluid Transfer Assembly	DOW SILICONES CORPORATION	10/23/2006 11173988.4	2383502	11/20/2013 602006039391.1
DC10284-DE-ETD[2]	Germany	Fluid Transfer Assembly	DOW SILICONES CORPORATION	10/23/2006 11174007.2	2383503	05/29/2013 602006036619.1
DC10284-EP-ETD	European (Patents)	Fluid Transfer Assembly	DOW SILICONES CORPORATION	10/23/2006 11173988.4	2383502	11/20/2013 2383502
DC10284-EP-ETD[2]	European (Patents)	Fluid Transfer Assembly	DOW SILICONES CORPORATION	10/23/2006 11174007.2	2383503	05/29/2013 2383503
DC10284-FR-EPT	France	Fluid Transfer Assembly	DOW SILICONES CORPORATION	10/23/2006 06826606.3	1952052	08/27/2014 1952052
DC10284-FR-ETD	France	Fluid Transfer Assembly	DOW SILICONES CORPORATION	10/23/2006 11174007.2	2383503	05/29/2013 2383503
DC10284-FR-ETD[2]	France	Fluid Transfer Assembly	DOW SILICONES CORPORATION	10/23/2006 11173988.4	2383502	11/20/2013 2383502
DC10284-GB-EPT	United Kingdom	Fluid Transfer Assembly	DOW SILICONES CORPORATION	10/23/2006 06826606.3	1952052	08/27/2014 1952052
DC10284-JP-PCT	Japan	Fluid Transfer Assembly	DOW SILICONES CORPORATION	10/23/2006 2008536620	2009512506	06/21/2013 5296546
DC10284-US-PCT	United States Of America	Fluid Transfer Assembly	DOW SILICONES CORPORATION	10/23/2006 12/090815	20080277926	04/23/2013 8424923
DC10385-CN-PCT	China	A Silicone Acrylate Hybrid Composition And Method of Making Same	DOW SILICONES CORPORATION	06/06/2007 200780029255.9	101501088	11/30/2011 200780029255.9
DC10385-DE-EPT	Germany	A Silicone Acrylate Hybrid Composition And Method of Making Same	DOW SILICONES CORPORATION	06/06/2007 07809357.2	2024406	08/01/2012 602007024394.7

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DC10385-DK-EPT	Denmark	and Method of Making Same	DOW SILICONES CORPORATION	06/06/2007 07809357.2	2024406	08/01/2012 2024406
DC10385-FR-EPT	France	A Silicone Acrylate Hybrid Composition and Method of Making Same	DOW SILICONES CORPORATION	06/06/2007 07809357.2	2024406	08/01/2012 2024406
DC10385-GB-EPT	United Kingdom	A Silicone Acrylate Hybrid Composition and Method of Making Same	DOW SILICONES CORPORATION	06/06/2007 07809357.2	2024406	08/01/2012 2024406
DC10385-IN-NP	India	A Silicone Acrylate Hybrid Composition and Method of Making Same	DOW SILICONES CORPORATION	10/20/2012 4382/CHE/2012		
DC10385-IN-NP[2]	India	A Silicone Acrylate Hybrid Composition and Method of Making Same	DOW SILICONES CORPORATION	11/28/2012 4958/CHE/2012		
DC10385-IN-PCT	India	A Silicone Acrylate Hybrid Composition and Method of Making Same	DOW SILICONES CORPORATION	06/06/2007 4944/KOLNP/2008		05/08/2015 266477
DC10385-JP-DIV	Japan	A Silicone Acrylate Hybrid Composition and Method of Making Same	DOW SILICONES CORPORATION	08/02/2013 2013161212	2014-015614	11/28/2014 5654100
DC10385-JP-NP	Japan	A Silicone Acrylate Hybrid Composition and Method of Making Same	DOW SILICONES CORPORATION	10/22/2012 2012-233020	2013-087289	03/17/2017 6108759
DC10385-KR-NP	SOUTH KOREA	A Silicone Acrylate Hybrid Composition and Method of Making Same	DOW SILICONES CORPORATION	10/22/2012 2012-0117546	2013-0044380	
DC10385-KR-NP[2]	SOUTH KOREA	A Silicone Acrylate Hybrid Composition and Method of Making Same	DOW SILICONES CORPORATION	11/29/2012 2012-0137365	2013-0060161	
DC10385-KR-PCT	SOUTH KOREA	A Silicone Acrylate Hybrid Composition and Method of Making Same	DOW SILICONES CORPORATION	06/06/2007 20087030476		08/14/2014 1432698
DC10385-SE-EPT	Sweden	A Silicone Acrylate Hybrid Composition and Method of Making Same	DOW SILICONES CORPORATION	06/06/2007 07809357.2	2024406	08/01/2012 2024406
DC10385-US-CIP	United States Of America	A Silicone Acrylate Hybrid Composition and Method of Making Same	DOW SILICONES CORPORATION	10/21/2011 13/278979	20120108560	10/29/2013 8569416
DC10385-US-CIP[2]	United States Of America	A Silicone Acrylate Hybrid Composition and Method of Making Same	DOW SILICONES CORPORATION	11/29/2011 13/306467	20120114737	12/24/2013 8614278
DC10385-US-PCT	United States Of America	A Silicone Acrylate Hybrid Composition and Method of Making Same	DOW SILICONES CORPORATION	06/06/2007 12/303362	20090196911	02/28/2012 8124689
DC10449-AT-EPT	Austria	Improved Carrier Lifetimes Method of Manufacturing Substrates Having	DOW SILICONES CORPORATION	07/17/2007 07810534.3	2044244	05/08/2013 2044244
DC10449-CA-PCT	Canada	Improved Carrier Lifetimes Method of Manufacturing Substrates Having	DOW SILICONES CORPORATION	07/17/2007 2657929		11/04/2014 2657929
DC10449-CN-DIV	China	Improved Carrier Lifetimes Method of Manufacturing Substrates Having	DOW SILICONES CORPORATION	07/17/2007 201210002807.X	102517631A	04/01/2015 201210002807.X
DC10449-DE-EPT	Germany	Improved Carrier Lifetimes Method of Manufacturing Substrates Having	DOW SILICONES CORPORATION	07/17/2007 07810534.3	2044244	05/08/2013 602007030360.5
DC10449-FR-EPT	France	Improved Carrier Lifetimes Method of Manufacturing Substrates Having	DOW SILICONES CORPORATION	07/17/2007 07810534.3	2044244	05/08/2013 2044244
DC10449-GB-EPT	United Kingdom	Improved Carrier Lifetimes	DOW SILICONES CORPORATION	07/17/2007 07810534.3	2044244	05/08/2013 2044244

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DC10449-JT- EPT	Italy	Method of Manufacturing Substrates Having Improved Carrier Lifetimes	DOW SILICONES CORPORATION	07/17/2007 07810534.3	2044244	05/08/2013 502013902181744
DC10449-JP- PCT	Japan	Method of Manufacturing Substrates Having Improved Carrier Lifetimes	DOW SILICONES CORPORATION	07/17/2007 2009520806	2009544171	
DC10449-KR- PCT	SOUTH KOREA	Method of Manufacturing Substrates Having Improved Carrier Lifetimes	DOW SILICONES CORPORATION	07/17/2007 20097001023		07/08/2014 101419279
DC10449-SE- EPT	Sweden	Method of Manufacturing Substrates Having Improved Carrier Lifetimes	DOW SILICONES CORPORATION	07/17/2007 07810534.3	2044244	05/08/2013 2044244
DC10449-US- CIP	United States Of America	Method of Manufacturing Substrates Having Improved Carrier Lifetimes	DOW SILICONES CORPORATION	01/18/2013 13/745066	20140203297	05/10/2016 9337027
DC10657-JP- PCT	Japan	Method to Manufacture Large Uniform Ingots of Silicon Carbide by Sublimation/Condensati on Processes	DOW SILICONES CORPORATION	10/08/2008 2010538004	2011506253	04/18/2014 5524855
DC10657-KR- PCT	SOUTH KOREA	Method to Manufacture Large Uniform Ingots of Silicon Carbide by Sublimation/Condensati on Processes	DOW SILICONES CORPORATION	10/08/2008 20107014917	20100100944	10/29/2015 101566020
DC10657-RU- PCT	Russian Federation	Method to Manufacture Large Uniform Ingots of Silicon Carbide by Sublimation/Condensati on Processes	DOW SILICONES CORPORATION	10/08/2008 2010123917		10/10/2013 2495163
DC10657-SG- PCT	Singapore	Method to Manufacture Large Uniform Ingots of Silicon Carbide by Sublimation/Condensati on Processes	DOW SILICONES CORPORATION	10/08/2008 201004127.5		03/28/2013 162266
DC10657-TW- NP	Taiwan	Method to Manufacture Large Uniform Ingots of Silicon Carbide by Sublimation/Condensati on Processes	DOW SILICONES CORPORATION	10/09/2008 097139066	200932964	06/21/2014 I441963
DC10657-US- PCT	United States Of America	Method to Manufacture Large Uniform Ingots of Silicon Carbide by Sublimation/Condensati on Processes	DOW SILICONES CORPORATION	10/08/2008 12/744532	20120114545	07/01/2014 8765091
DC10684-BR- PCT	Brazil	Process For Reduction Of Friction	DOW SILICONES CORPORATION	05/14/2009 P10911885-3		
DC10684-DE- EPT	Germany European	Process For Reduction Of Friction	DOW SILICONES CORPORATION	05/14/2009 09745803.8	2276815	12/27/2017 602009050110.0
DC10684-EP- EPT	(Patents)	Process For Reduction Of Friction	DOW SILICONES CORPORATION	05/14/2009 09745803.8	2276815	12/27/2017 2276815
DC10684-FR- EPT	France	Process For Reduction Of Friction	DOW SILICONES CORPORATION	05/14/2009 09745803.8	2276815	12/27/2017 2276815
DC10684-IT- EPT	Italy	Process For Reduction Of Friction	DOW SILICONES CORPORATION	05/14/2009 09745803.8	2276815	12/27/2017 50201800009102
DC10684-JP- PCT	Japan	Process For Reduction Of Friction	DOW SILICONES CORPORATION	05/14/2009 2011-508926	2011-522912	09/19/2014 5615806
DC10684-KR- PCT	SOUTH KOREA	Process For Reduction Of Friction	DOW SILICONES CORPORATION	05/14/2009 2010-7025162		
DC10684-NL- EPT	Netherlands	Process For Reduction Of Friction	DOW SILICONES CORPORATION	05/14/2009 09745803.8	2276815	12/27/2017 2276815
DC10730-DE- EPT	Germany	Photovoltaic Cell Module and Method of Forming	DOW SILICONES CORPORATION	10/29/2009 09744574.6	2351102	08/20/2014 602009026143.6
DC10730-FR- EPT	France	Photovoltaic Cell Module and Method of Forming	DOW SILICONES CORPORATION	10/29/2009 09744574.6	2351102	08/20/2014 2351102

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DC10730-JP-DIV	Japan	Photovoltaic Cell Module and Method of Forming Photovoltaic Cell	DOW SILICONES CORPORATION	10/29/2009 2012-236740	03/28/2014 5509293
DC10730-KR-DIV	SOUTH KOREA	Module and Method of Forming Photovoltaic Cell	DOW SILICONES CORPORATION	10/29/2012 2012-7026755	2012-7026755 05/24/2016 101625545
DC10730-NL-EPT	Netherlands	Module and Method of Forming Photovoltaic Cell	DOW SILICONES CORPORATION	10/29/2009 09744574.6	2351102 08/20/2014 2351102
DC10730-TW-DIV	Taiwan	Module and Method of Forming Photovoltaic Cell	DOW SILICONES CORPORATION	10/30/2009 101138811	201308643 12/11/2015 I513025
DC10730-TW-DIV[2]	Taiwan	Module and Method of Forming Photovoltaic Cell	DOW SILICONES CORPORATION	10/30/2009 101138810	11/11/2015 I508317
DC10730-TW-NP	Taiwan	Module and Method of Forming Photovoltaic Cell	DOW SILICONES CORPORATION	10/30/2009 098137024	11/11/2015 I508313
DC10730-US-CNT	United States Of America	Module and Method of Forming Method of Reducing Memory Effects in Semiconductor Epitaxy	DOW SILICONES CORPORATION	02/25/2015 14/630998	2015-0171249 12/12/2017 9842952
DC10739-CN-PCT	China	Semiconductor Epitaxy Method of Reducing Memory Effects in Semiconductor Epitaxy	DOW SILICONES CORPORATION	05/29/2009 200980120374.4	102057078A 04/01/2015 200980120374.4
DC10739-JP-PCT	Japan	Semiconductor Epitaxy Method of Reducing Memory Effects in Semiconductor Epitaxy	DOW SILICONES CORPORATION	05/29/2009 2011-512535	2011-523214 02/21/2014 5478616
DC10739-RU-PCT	Russian Federation	Memory Effects in Semiconductor Epitaxy Method of Reducing Memory Effects in Semiconductor Epitaxy	DOW SILICONES CORPORATION	05/29/2009 2010149457	04/22/2014 2520283
DC10739-SG-PCT	Singapore	Memory Effects in Semiconductor Epitaxy Method of Reducing Memory Effects in Semiconductor Epitaxy	DOW SILICONES CORPORATION	05/29/2009 201008219-6	05/31/2013 166904
DC10739-TW-NP	Taiwan	Memory Effects in Semiconductor Epitaxy Method of Reducing Memory Effects in Semiconductor Epitaxy	DOW SILICONES CORPORATION	06/04/2009 098118587	201013754 06/21/2013 I399795
DC10739-US-PCT	United States Of America	Memory Effects in Semiconductor Epitaxy	DOW SILICONES CORPORATION	05/29/2009 12/993938	20110073874 01/01/2013 8343854
DC10794-CN-PCD	China	CVD Precursors	DOW SILICONES CORPORATION	08/11/2009 201310392992.2	103467506 03/23/2016 201310392992.2
DC10794-CN-PCT	China	CVD Precursors	DOW SILICONES CORPORATION	08/11/2009 200980141783.2	102187011 04/09/2014 200980141783.2
DC10794-DE-EPT	Germany	CVD Precursors	DOW SILICONES CORPORATION	08/11/2009 09822363.9	2373830 04/30/2014 602090923746.2
DC10794-JP-PCD	Japan	CVD Precursors	DOW SILICONES CORPORATION	08/30/2013 2013-179767	10/02/2015 5816235
DC10794-JP-PCT	Japan	CVD Precursors	DOW SILICONES CORPORATION	08/11/2009 2011-532103	2012-506147 03/07/2014 5491512
DC10794-KR-PCD	SOUTH KOREA	CVD Precursors	DOW SILICONES CORPORATION	03/03/2016 2016-7005023	07/07/2016 10-1639432
DC10794-KR-PCT	SOUTH KOREA	CVD Precursors	DOW SILICONES CORPORATION	08/11/2009 2011-7011237	2011-0084517
DC10794-SG-PCT	Singapore	CVD Precursors	DOW SILICONES CORPORATION	08/11/2009 201102595-4	10/31/2013 170407
DC10794-TW-NP	Taiwan	CVD Precursors	DOW SILICONES CORPORATION	09/10/2009 098130566	201016878 01/11/2015 I468542
DC10794-US-CNT	United States Of America	CVD Precursors	DOW SILICONES CORPORATION	05/19/2014 14/280770	20140256159 08/25/2015 9117664
DC10794-US-PCT	United States Of America	CVD Precursors Film Forming, Silicone Compositions	DOW SILICONES CORPORATION	08/11/2009 13/122745	20110195582 07/08/2014 8772524
DC10924-CN-PCT	China	Containing Compositions Film Forming, Silicone	DOW SILICONES CORPORATION	07/02/2010 201080022977.3	102449073 11/13/2013 201080022977.3
DC10924-DE-EPT	Germany	Containing Compositions Film Forming, Silicone	DOW SILICONES CORPORATION	07/02/2010 I0731884.2	2449031 06/04/2014 602010016447.0
DC10924-FR-EPT	France	Containing Compositions Film Forming, Silicone	DOW SILICONES CORPORATION	07/02/2010 10731884.2	2449031 06/04/2014 2449031
DC10924-GB-EPT	United Kingdom	Containing Compositions Film Forming, Silicone	DOW SILICONES CORPORATION	07/02/2010 10731884.2	2449031 06/04/2014 2449031
DC10924-US-PCT	United States Of America	Containing Compositions Film Forming, Silicone	DOW SILICONES CORPORATION	07/02/2010 13/379893	20120095109 08/04/2015 9096721
DC11350-CN-PCT	China	Topical Formulation Compositions Containing Silicone Based Excipients To Deliver Actives To A Substrate	DOW SILICONES CORPORATION	03/11/2013 201380021411.2	104271160 08/08/2017 201380021411.2
DC11350-EP-EPT	European Procedure (Patents)	Based Excipients To Deliver Actives To A Substrate Topical Formulation	DOW SILICONES CORPORATION	03/11/2013 13713613.1	2841106A

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DC11350-JP-		Compositions Containing Silicone Based Excipients To Deliver Actives To A	DOW SILICONES CORPORATION	03/11/2013 2015-508959	2015-514801	02/17/2017 6093007
PCT	Japan	Substrate	DOW SILICONES CORPORATION	12/20/2012 201280070705.X	104204119	10/12/2016 201280070705.X
DC11353-CN-		Solid State Light And	DOW SILICONES CORPORATION	12/20/2012 12813672.8	2798024	07/20/2016 602012020823.6
PCT	China	Method Of Forming Solid State Light And	DOW SILICONES CORPORATION	12/20/2012 2014-550382	2015-510257	09/09/2016 6001676
DC11353-DE-		Method Of Forming Solid State Light And	DOW SILICONES CORPORATION	12/20/2012 2014-7021246		
EPT	Germany	Method Of Forming Solid State Light And	DOW SILICONES CORPORATION	12/20/2012 14/369981	20150001567	04/07/2015 9000472
DC11353-JP-		Method Of Forming Solid State Light And	DOW SILICONES CORPORATION	12/20/2012 14/369981	20150001567	04/07/2015 9000472
PCT	Japan	Method Of Forming Solid State Light And	DOW SILICONES CORPORATION	12/20/2012 14/369981	20150001567	04/07/2015 9000472
DC11353-KR-		Method Of Forming Solid State Light And	DOW SILICONES CORPORATION	12/20/2012 14/369981	20150001567	04/07/2015 9000472
PCT	SOUTH KOREA	Method Of Forming Solid State Light And	DOW SILICONES CORPORATION	12/20/2012 14/369981	20150001567	04/07/2015 9000472
DC11353-US-	United States Of	Solid State Light And	DOW SILICONES CORPORATION	12/20/2012 14/369981	20150001567	04/07/2015 9000472
PCT	America	Method Of Forming Method Of Forming A Light Transmitting Sheet Of A Solid State Light	DOW SILICONES CORPORATION	01/16/2013 201380013063.4	104159726	01/18/2017 2013800130634
DC11357-CN-		Method Of Forming A Light Transmitting Sheet Of A Solid State Light	DOW SILICONES CORPORATION	01/16/2013 201380013063.4	104159726	01/18/2017 2013800130634
PCT	China	Method Of Forming A Light Transmitting Sheet Of A Solid State Light	DOW SILICONES CORPORATION	01/16/2013 13703193.6	2804747	
DC11357-EP-	European (Patents)	Procedure Sheet Of A Solid State Light	DOW SILICONES CORPORATION	01/16/2013 13703193.6	2804747	
EPT		Method Of Forming A Light Transmitting Sheet Of A Solid State Light	DOW SILICONES CORPORATION	01/16/2013 2014-552390	2015-513328	03/23/2018 6309898
DC11357-JP-		Method Of Forming A Light Transmitting Sheet Of A Solid State Light	DOW SILICONES CORPORATION	01/16/2013 2014-702437		
PCT	Japan	Method Of Forming A Light Transmitting Sheet Of A Solid State Light	DOW SILICONES CORPORATION	01/16/2013 2014-702437		
DC11357-KR-		Sheet Of A Solid State Light OPTICAL ARTICLE	DOW SILICONES CORPORATION	01/16/2013 2014-702437		
PCT	SOUTH KOREA	Sheet Of A Solid State Light OPTICAL ARTICLE	DOW SILICONES CORPORATION	01/16/2013 14/372465	20150290887	06/27/2017 9688035
DC11374-CN-		Curable Compositions Of Resin-Linear Organosiloxane Block Copolymers	DOW SILICONES CORPORATION	12/14/2012 201280069712.8	104114656A	08/25/2017 201280069712.8
PCT	China	Curable Compositions Of Resin-Linear Organosiloxane Block Copolymers	DOW SILICONES CORPORATION	12/14/2012 12815889.6	2791263	08/31/2016 602012022476.2
DC11374-DE-		Curable Compositions Of Resin-Linear Organosiloxane Block Copolymers	DOW SILICONES CORPORATION	12/14/2012 12815889.6	2791263	08/31/2016 602012022476.2
EPT	Germany	Curable Compositions Of Resin-Linear Organosiloxane Block Copolymers	DOW SILICONES CORPORATION	12/14/2012 2014-547475		
DC11374-JP-		Curable Compositions Of Resin-Linear Organosiloxane Block Copolymers	DOW SILICONES CORPORATION	12/14/2012 10-2014-7018537		
PCT	Japan	Curable Compositions Of Resin-Linear Organosiloxane Block Copolymers	DOW SILICONES CORPORATION	12/14/2012 10-2014-7018537		
DC11374-KR-		Curable Compositions Of Resin-Linear Organosiloxane Block Copolymers	DOW SILICONES CORPORATION	12/14/2012 10-2014-7018537		
PCT	SOUTH KOREA	Curable Compositions Of Resin-Linear Organosiloxane Block Copolymers	DOW SILICONES CORPORATION	12/14/2012 12815889.6	2791263	08/31/2016 2791263
DC11374-NL-		Curable Compositions Of Resin-Linear Organosiloxane Block Copolymers	DOW SILICONES CORPORATION	12/14/2012 12815889.6	2791263	08/31/2016 2791263
EPT	Netherlands	Curable Compositions Of Resin-Linear Organosiloxane Block Copolymers	DOW SILICONES CORPORATION	12/14/2012 14/364654	20140357827	05/16/2017 9650472
DC11374-US-	United States Of	Curable Compositions Of Resin-Linear Organosiloxane Block Copolymers	DOW SILICONES CORPORATION	12/14/2012 14/364654	20140357827	05/16/2017 9650472
PCT	America	Curable Compositions Of Resin-Linear Organosiloxane Block Copolymers	DOW SILICONES CORPORATION	03/14/2013 14/386213	20150112011	11/03/2015 9175140
DC11462-US-		Curable Compositions Of Resin-Linear Organosiloxane Block Copolymers	DOW SILICONES CORPORATION	11/12/2013 201380057948.4	104769729	08/29/2017 201380057948.4
PCT	United States Of	Photovoltaic Cell Module	DOW SILICONES CORPORATION	11/12/2013 13795398.0	2917943	10/05/2016 602013012539.2
DC11520-CN-		Photovoltaic Cell Module	DOW SILICONES CORPORATION	11/12/2013 2015542009	2016-504758	
PCT	China	Photovoltaic Cell Module	DOW SILICONES CORPORATION	11/12/2013 10-2015-7012077	2015-0084826	
DC11520-DE-		Photovoltaic Cell Module	DOW SILICONES CORPORATION	11/12/2013 201380057521.4	104769043	08/08/2017 201380057521.4
EPT	Germany	Photovoltaic Cell Module	DOW SILICONES CORPORATION	11/12/2013 201380057521.4	104769043	08/08/2017 201380057521.4
DC11520-JP-		Photovoltaic Cell Module	DOW SILICONES CORPORATION	11/12/2013 201380057521.4	104769043	08/08/2017 201380057521.4
PCT	Japan	Photovoltaic Cell Module	DOW SILICONES CORPORATION	11/12/2013 201380057521.4	104769043	08/08/2017 201380057521.4
DC11520-KR-		Photovoltaic Cell Module	DOW SILICONES CORPORATION	11/12/2013 201380057521.4	104769043	08/08/2017 201380057521.4
PCT	SOUTH KOREA	Photovoltaic Cell Module	DOW SILICONES CORPORATION	11/12/2013 201380057521.4	104769043	08/08/2017 201380057521.4
DC11521-CN-		Method Of Forming An Electronic Article	DOW SILICONES CORPORATION	11/12/2013 201380057521.4	104769043	08/08/2017 201380057521.4
PCT	China	Method Of Forming An Electronic Article	DOW SILICONES CORPORATION	11/12/2013 201380057521.4	104769043	08/08/2017 201380057521.4

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DC11521-EP-	European Procedure	Method Of Forming An Electronic Article	DOW SILICONES CORPORATION	11/12/2013 13798474.6	2917282
DC11521-JP-	(Patents)	Method Of Forming An Electronic Article	DOW SILICONES CORPORATION	11/12/2013 2018-76050	
PCD	Japan	Electronic Article	CORPORATION		
DC11521-JP-		Method Of Forming An Electronic Article	DOW SILICONES CORPORATION		
PCT	Japan	Method Of Forming An Electronic Article	DOW SILICONES CORPORATION	11/12/2013 2015542016	07/06/2018 6363089
DC11521-KR-		Method Of Forming An Electronic Article	DOW SILICONES CORPORATION		
PCT	SOUTH KOREA	Electronic Article	CORPORATION	11/12/2013 20157012116	
DC11521-US-	United States Of America	Method Of Forming An Electronic Article	DOW SILICONES CORPORATION	11/12/2013 14/440754	20150263208 04/12/2016 9312416
DC11526-CN-		Flat SiC Semiconductor Substrate	DOW SILICONES CORPORATION	09/10/2013 201380060888.1	4813439A 04/12/2017 20138006888.1
PCT	China	Flat SiC Semiconductor Substrate	DOW SILICONES CORPORATION		
DC11526-DE-		Flat SiC Semiconductor Substrate	DOW SILICONES CORPORATION	09/10/2013 13765897.7	2912681 10/26/2016 602013013271.2
EPT	Germany	Flat SiC Semiconductor Substrate	DOW SILICONES CORPORATION		
DC11526-FR-		Flat SiC Semiconductor Substrate	DOW SILICONES CORPORATION	09/10/2013 13765897.7	2912681 10/26/2016 2912681
EPT	France	Flat SiC Semiconductor Substrate	DOW SILICONES CORPORATION		
DC11526-GB-		Flat SiC Semiconductor Substrate	DOW SILICONES CORPORATION	09/10/2013 13765897.7	2912681 10/26/2016 2912681
EPT	United Kingdom	Flat SiC Semiconductor Substrate	DOW SILICONES CORPORATION		
DC11526-IT-		Flat SiC Semiconductor Substrate	DOW SILICONES CORPORATION	09/10/2013 13765897.7	2912681 10/26/2016 50201700006480
EPT	Italy	Flat SiC Semiconductor Substrate	DOW SILICONES CORPORATION		
DC11526-US-	United States Of America	Flat SiC Semiconductor Substrate	DOW SILICONES CORPORATION	03/11/2015 14/644980	20150194319 10/20/2015 9165779
DIV		Flat SiC Semiconductor Substrate	DOW SILICONES CORPORATION		
DC11526-US-	United States Of America	Flat SiC Semiconductor Substrate	DOW SILICONES CORPORATION	08/06/2013 13/959896	20140117380 04/28/2015 9018639
NP		Flat SiC Semiconductor Substrate	DOW SILICONES CORPORATION		
DC11571-CN-		Polyolefin And Organopolysiloxane Production Of Blend Of	DOW SILICONES CORPORATION	09/19/2013 201380047978.7	4769016A 06/23/2017 201380047978.7
PCT	China	Polyolefin And Organopolysiloxane Production Of Blend Of	DOW SILICONES CORPORATION		
DC11571-DE-		Polyolefin And Organopolysiloxane Production Of Blend Of	DOW SILICONES CORPORATION	09/19/2013 13766015.5	2898002 05/23/2018 2898002
EPT	Germany	Polyolefin And Organopolysiloxane Production Of Blend Of	DOW SILICONES CORPORATION		
DC11571-EP-	European Procedure	Polyolefin And Organopolysiloxane Production Of Blend Of	DOW SILICONES CORPORATION	09/19/2013 13766015.5	2898002 05/23/2018 2898002
EPT	(Patents)	Polyolefin And Organopolysiloxane Production Of Blend Of	DOW SILICONES CORPORATION		
DC11571-ES-		Polyolefin And Organopolysiloxane Production Of Blend Of	DOW SILICONES CORPORATION	09/19/2013 13766015.5	2898002 05/23/2018 2898002
EPT	Spain	Polyolefin And Organopolysiloxane Production Of Blend Of	DOW SILICONES CORPORATION		
DC11571-FR-		Polyolefin And Organopolysiloxane Production Of Blend Of	DOW SILICONES CORPORATION	09/19/2013 13766015.5	2898002 05/23/2018 2898002
EPT	France	Polyolefin And Organopolysiloxane Production Of Blend Of	DOW SILICONES CORPORATION		
DC11571-GB-		Polyolefin And Organopolysiloxane Production Of Blend Of	DOW SILICONES CORPORATION	09/19/2013 13766015.5	2898002 05/23/2018 2898002
EPT	United Kingdom	Polyolefin And Organopolysiloxane Production Of Blend Of	DOW SILICONES CORPORATION		
DC11571-IT-		Polyolefin And Organopolysiloxane Production Of Blend Of	DOW SILICONES CORPORATION	09/19/2013 13766015.5	2898002 05/23/2018 50201800024656
EPT	Italy	Polyolefin And Organopolysiloxane Production Of Blend Of	DOW SILICONES CORPORATION		
DC11571-KR-		Polyolefin And Organopolysiloxane Production Of Blend Of	DOW SILICONES CORPORATION	09/19/2013 10-2015-700956	
PCT	SOUTH KOREA	Polyolefin And Organopolysiloxane Production Of Blend Of	DOW SILICONES CORPORATION		
DC11571-NL-		Polyolefin And Organopolysiloxane Production Of Blend Of	DOW SILICONES CORPORATION	09/19/2013 13766015.5	2898002 05/23/2018 2898002
EPT	Netherlands	Polyolefin And Organopolysiloxane Production Of Blend Of	DOW SILICONES CORPORATION		
DC11571-PL-		Polyolefin And Organopolysiloxane Production Of Blend Of	DOW SILICONES CORPORATION	09/19/2013 13766015.5	2898002 05/23/2018 2898002
EPT	Poland	Polyolefin And Organopolysiloxane Production Of Blend Of	DOW SILICONES CORPORATION		
DC11571-SE-		Polyolefin And Organopolysiloxane Production Of Blend Of	DOW SILICONES CORPORATION	09/19/2013 13766015.5	2898002 05/23/2018 2898002
EPT	Sweden	Polyolefin And Organopolysiloxane Production Of Blend Of	DOW SILICONES CORPORATION		
DC11571-TR-		Polyolefin And Organopolysiloxane Production Of Blend Of	DOW SILICONES CORPORATION	09/19/2013 13766015.5	2898002 05/23/2018 2898002
EPT	Turkey	Polyolefin And Organopolysiloxane Production Of Blend Of	DOW SILICONES CORPORATION		
DC11571-US-	United States Of America	Polyolefin And Organopolysiloxane High Voltage Power	DOW SILICONES CORPORATION	09/19/2013 14/429004	20150225557 12/27/2016 9527988
PCT		High Voltage Power			
DC11578-CN-		Semiconductor Devices On SiC	DOW SILICONES CORPORATION	09/10/2013 201380020805.6	4246979A 11/23/2016 201380020805.6
PCT	China	On SiC			
DC11578-KR-		On SiC	DOW SILICONES CORPORATION	09/10/2013 20147027127	07/22/2015 1539927
PCT	SOUTH KOREA	High Voltage Power			
DC11578-US-	United States Of America	Semiconductor Devices On SiC	DOW SILICONES CORPORATION	09/16/2014 14/487774	20150333125 05/10/2016 9337277
CNT		High Voltage Power			
DC11578-US-	United States Of America	Semiconductor Devices On SiC	DOW SILICONES CORPORATION	08/06/2013 13/959855	20140070234 10/14/2014 8860040
NP		High Voltage Power			

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DC11629-CN-PCT	China	2-Aminimidazole-Functional Silicone Compositions And Methods Of Making The Same	DOW SILICONES CORPORATION	03/13/2014 201480014328.7	105189672	08/25/2017 201480014328.7
DC11629-DE-EPT	Germany	2-Aminimidazole-Functional Silicone Compositions And Methods Of Making The Same	DOW SILICONES CORPORATION	03/13/2014 14720790.6	2970715	10/26/2016 602014004499.9
DC11629-FR-EPT	France	2-Aminimidazole-Functional Silicone Compositions And Methods Of Making The Same	DOW SILICONES CORPORATION	03/13/2014 14720790.6	2970715	10/26/2016 2970715
DC11629-GB-EPT	United Kingdom	2-Aminimidazole-Functional Silicone Compositions And Methods Of Making The Same	DOW SILICONES CORPORATION	03/13/2014 14720790.6	2970715	10/26/2016 2970715
DC11629-KR-PCT	SOUTH KOREA	2-Aminimidazole-Functional Silicone Compositions And Methods Of Making The Same	DOW SILICONES CORPORATION	03/13/2014 2015-7025344		
DC11629-US-PCT	United States Of America	Methods Of Making The Same SIC Crystal and Wafer Cut from Crystal with Low Dislocation	DOW SILICONES CORPORATION	03/13/2014 14/773762	20160024257	08/23/2016 9422404
DC11662-CN-PCT	China	SIC Crystal and Wafer Density	DOW SILICONES CORPORATION	12/20/2013 201380074914.6		
DC11662-EP-EPT	European Procedure (Patents)	Cut from Crystal with Low Dislocation Density SIC Crystal and Wafer	DOW SILICONES CORPORATION	12/20/2013 13824055.1	2954101	
DC11662-JP-PCT	Japan	Cut from Crystal with Low Dislocation Density SIC Crystal and Wafer	DOW SILICONES CORPORATION	12/20/2013 2015-556013	2016-506902	
DC11662-KR-PCT	SOUTH KOREA	Cut from Crystal with Low Dislocation Density SIC Crystal and Wafer	DOW SILICONES CORPORATION	12/20/2013 10-2015-7024105		
DC11662-US-DIV	United States Of America	Cut from Crystal with Low Dislocation Density SIC Crystal and Wafer	DOW SILICONES CORPORATION	01/30/2017 15/419993	20170137963	
DC11662-US-NP	United States Of America	Low Dislocation Density	DOW SILICONES CORPORATION	10/18/2013 14/058167	20140220296	10/24/2017 9797064
DC11663-CN-PCT	China	Method To Reduce Dislocations in SIC Crystal Growth	DOW SILICONES CORPORATION	12/20/2013 201380074938.1	5189835A	05/24/2017 201380074938.1
DC11663-EP-EPT	European Procedure (Patents)	Method To Reduce Dislocations in SIC Crystal Growth	DOW SILICONES CORPORATION	12/20/2013 13818955.0	2943602	
DC11663-JP-PCT	Japan	Method To Reduce Dislocations in SIC Crystal Growth	DOW SILICONES CORPORATION	12/20/2013 2015-556941	2016-507462	02/09/2018 6285963
DC11663-KR-PCT	SOUTH KOREA	Method To Reduce Dislocations in SIC Crystal Growth	DOW SILICONES CORPORATION	12/20/2013 2015-7024047	2015-0107895	06/27/2016 1016354380000
DC11663-US-NP	United States Of America	Dislocations in SIC Crystal Growth	DOW SILICONES CORPORATION	07/08/2013 13/937149	20140220325	04/28/2015 9017804
DC11664-CN-PCT	China	Dislocations in SIC Crystal With Low Density	DOW SILICONES CORPORATION	12/20/2013 201380074470.6	5008596A	
DC11664-EP-EPT	European Procedure (Patents)	Dislocation Density SIC Crystal With Low	DOW SILICONES CORPORATION	12/20/2013 13821355.8	2954100	
DC11664-JP-PCT	Japan	Dislocation Density SIC Crystal With Low	DOW SILICONES CORPORATION	12/20/2013 2015-556014	2016-508948	
DC11664-KR-PCT	SOUTH KOREA	Dislocation Density SIC Crystal With Low	DOW SILICONES CORPORATION	12/20/2013 2015-024104	2015-116885	
DC11664-US-DIV	United States Of America	Dislocation Density SIC Crystal With Low	DOW SILICONES CORPORATION	01/31/2017 15/421220		
DC11664-US-NP	United States Of America	Dislocation Density SIC Crystal With Low	DOW SILICONES CORPORATION	08/09/2013 13/963989	20140220298	08/22/2017 9738991
DC11726-CN-PCT	China	Silicone Acrylate Compositions And Methods Of Preparing The Same	DOW SILICONES CORPORATION	01/29/2016 201680015769.8		

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DC11726-EP-EPT	European Patent	Silicone Acrylate Compositions And Methods Of Preparing The Same	DOW SILICONES CORPORATION	01/29/2016	16744149.2	3250618	
DC11726-IN-PCT	India	Silicone Acrylate Compositions And Methods Of Preparing The Same	DOW SILICONES CORPORATION	01/29/2016	201717027908	201717027908	
DC11726-JP-PCT	Japan	Silicone Acrylate Compositions And Methods Of Preparing The Same	DOW SILICONES CORPORATION	01/29/2016	2017-538574		
DC11726-KR-PCT	SOUTH KOREA	Silicone Acrylate Compositions And Methods Of Preparing The Same	DOW SILICONES CORPORATION	01/29/2016	10-2017-7023044	10-2017-0106428	
DC11726-US-PCT	United States Of America	Silicone Resin	DOW SILICONES CORPORATION	01/29/2016	15/532362	20170368179	
DC11727-CN-PCT	China	Composition For LED Devices	DOW SILICONES CORPORATION	02/21/2014	201480020682.0	105121556	
DC11727-DE-EPT	Germany European	Silicone Resin	DOW SILICONES CORPORATION	02/21/2014	14708752.2	2958961	05/16/2018 602014025503.5
DC11727-EP-EPT	Procedure (Patents)	Composition For LED Devices	DOW SILICONES CORPORATION	02/21/2014	14708752.2	2958961	05/16/2018 2958961
DC11727-JP-PCT	Japan	Silicone Resin	DOW SILICONES CORPORATION	02/21/2014	2015-558990		03/02/2018 6297070
DC11727-KR-PCD	SOUTH KOREA	Composition For LED Devices	DOW SILICONES CORPORATION	10/07/2016	10-2016-7024814		
DC11727-KR-PCT	SOUTH KOREA	Silicone Resin	DOW SILICONES CORPORATION	02/21/2014	10-2015-7022361		06/08/2017 10-1747160
DC11727-TW-NP	Taiwan	Composition For LED Devices	DOW SILICONES CORPORATION	02/21/2014	103105947	201439220	08/01/2018 I631185
DC11727-US-PCT	United States Of America	Silicone Resin	DOW SILICONES CORPORATION	02/21/2014	14/769131	20150376344	02/27/2018 9902811
DC11734-CN-PCT	China	High Scratch Resistance Properties	DOW SILICONES CORPORATION	03/02/2015	201580014989.4	106103577A	
DC11734-EP-EPT	European Procedure (Patents)	Method Of Producing A Silicone Masterbatch	DOW SILICONES CORPORATION	03/02/2015	15707619.1	3114168	
DC11734-GB-NP	United Kingdom	Composition Having High Scratch Resistance Properties	DOW SILICONES CORPORATION	12/02/2014	1421634.5		
DC11734-IN-PCT	India	Method Of Producing A Silicone Masterbatch	DOW SILICONES CORPORATION	03/02/2015	201617033637		
DC11734-JP-PCT	Japan	Composition Having High Scratch Resistance Properties	DOW SILICONES CORPORATION	03/02/2015	2016-572895		
DC11734-KR-PCT	SOUTH KOREA	Method Of Producing A Silicone Masterbatch	DOW SILICONES CORPORATION	03/02/2015	10-2016-7027516	10-2016-0141746	
DC11734-RU-PCT	Russian Federation	Composition Having High Scratch Resistance Properties	DOW SILICONES CORPORATION	03/02/2015	2016136182	2016136182	
DC11734-US-PCT	United States Of America	THERMOPLASTIC POLYMER	DOW SILICONES CORPORATION	03/02/2015	15/123278	20170058114	
DC11735-CN-PCT	China	MASTERBATCH SiC Substrate With SiC	DOW SILICONES CORPORATION	03/15/2014	201480002722.9	4718601A	04/26/2017 201480002722.9
DC11735-DE-EPT	Germany	SiC Substrate With SiC	DOW SILICONES CORPORATION	03/15/2014	14721146.0	2837020	05/17/2017 2837020

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DC11735-ES-		SiC Substrate With SiC	DOW SILICONES			
EPT	Spain	Epitaxial Film	CORPORATION	03/15/2014	14721146.0	2837020
DC11735-FI-		SiC Substrate With SiC	DOW SILICONES	03/15/2014	14721146.0	2837020
EPT	Finland	Epitaxial Film	CORPORATION	03/15/2014	14721146.0	2837020
DC11735-FR-		SiC Substrate With SiC	DOW SILICONES	03/15/2014	14721146.0	2837020
EPT	France	Epitaxial Film	CORPORATION	03/15/2014	14721146.0	2837020
DC11735-GB-		SiC Substrate With SiC	DOW SILICONES	03/15/2014	14721146.0	2837020
EPT	United Kingdom	Epitaxial Film	CORPORATION	03/15/2014	14721146.0	2837020
DC11735-IT-		SiC Substrate With SiC	DOW SILICONES	03/15/2014	14721146.0	2837020
EPT	Italy	Epitaxial Film	CORPORATION	03/15/2014	14721146.0	05/17/2017 502017000093402
DC11735-JP-		SiC Substrate With SiC	DOW SILICONES	03/15/2014	2015-523311	06/24/2016 5955463
PCT	Japan	Epitaxial Film	CORPORATION	03/15/2014	2015-523311	06/24/2016 5955463
DC11735-KR-		SiC Substrate With SiC	DOW SILICONES	03/15/2014	2015-7008990	06/17/2016 1016329470000
PCT	SOUTH KOREA	Epitaxial Film	CORPORATION	03/15/2014	2015-7008990	06/17/2016 1016329470000
DC11735-SE-		SiC Substrate With SiC	DOW SILICONES	03/15/2014	14721146.0	05/17/2017 2837020
EPT	Sweden	Epitaxial Film	CORPORATION	03/15/2014	14721146.0	05/17/2017 2837020
DC11735-US-	United States Of	SiC Substrate With SiC	DOW SILICONES	03/14/2014	14/213888	01/27/2015 8940614
PCT	America	Epitaxial Film	CORPORATION	03/14/2014	14/213888	01/27/2015 8940614
	European	Curable Silicone Composition, Cured Product Thereof, And Optical Semiconductor Device	DOW SILICONES CORPORATION	08/26/2014	14840431.2	3039079
DC11810-EP-	Procedure					
EPT	(Patents)					
DC11814-CN-		Tetrasilylpentasilane And Its Compositions, Methods And Uses	DOW SILICONES CORPORATION	09/03/2014	201480054107.2	105593233
PCT	China	2,2,4,4-				04/27/2018 201480054107.2
DC11814-DE-		Tetrasilylpentasilane And Its Compositions, Methods And Uses	DOW SILICONES CORPORATION	09/03/2014	14766329.8	3041850
EPT	Germany	2,2,4,4-				11/15/2017 602014017294.6
DC11814-EP-		Tetrasilylpentasilane And Its Compositions, Methods And Uses	DOW SILICONES CORPORATION	09/03/2014	14766329.8	3041850
EPT	(Patents)	2,2,4,4-				11/15/2017 3041850
DC11814-JP-		Tetrasilylpentasilane And Its Compositions, Methods And Uses	DOW SILICONES CORPORATION	09/03/2014	2016-540322	
PCT	Japan	2,2,4,4-				
DC11814-KR-		Tetrasilylpentasilane And Its Compositions, Methods And Uses	DOW SILICONES CORPORATION	09/03/2014	2016-7008588	2016-0052631
PCT	SOUTH KOREA	2,2,4,4-				
DC11814-TW-		Tetrasilylpentasilane And Its Compositions, Methods And Uses	DOW SILICONES CORPORATION	09/01/2014	103130048	201518210
NP	Taiwan	2,2,4,4-				09/01/2018 1634073
DC11814-US-	United States Of	Tetrasilylpentasilane And Its Compositions, Methods And Uses	DOW SILICONES CORPORATION	11/10/2017	15/809431	20180066140
CIP	America	2,2,4,4-				
DC11814-US-	United States Of	Tetrasilylpentasilane And Its Compositions, Methods And Uses	DOW SILICONES CORPORATION	09/03/2014	14/915404	20160207784
PCT	America	Anti-Friction Coating				03/27/2018 9926203
DC11842-CN-		For Dry Lubrication Of Engine Fasteners	DOW SILICONES CORPORATION	12/18/2014	201480071817.6	105873975A
PCT	China	Anti-Friction Coating				
DC11842-EP-	European	For Dry Lubrication Of Engine Fasteners	DOW SILICONES CORPORATION	12/18/2014	14825135.8	3083750
EPT	Procedure	Anti-Friction Coating				
DC11842-JP-		For Dry Lubrication Of Engine Fasteners	DOW SILICONES CORPORATION	12/18/2014	2016-541435	
PCT	Japan	Anti-Friction Coating				
DC11842-KR-		For Dry Lubrication Of Engine Fasteners	DOW SILICONES CORPORATION	12/18/2014	2016-7018801	
PCT	SOUTH KOREA	Anti-Friction Coating				
DC11842-US-	United States Of	For Dry Lubrication Of Engine Fasteners	DOW SILICONES CORPORATION	12/18/2014	15/105943	20160319211
PCT	America					
DC11847-CN-		Low Friction Resistance Polyoxymethylene Composition	DOW SILICONES CORPORATION	03/26/2015	201580016341.0	106133053
PCT	China					
	European	Low Friction Resistance Polyoxymethylene Composition	DOW SILICONES CORPORATION	03/26/2015	15712153.4	3126445
DC11847-EP-	Procedure					
EPT	(Patents)					
DC11847-JP-		Low Friction Resistance Polyoxymethylene Composition	DOW SILICONES CORPORATION	03/26/2015	2016-559988	
PCT	Japan					
DC11847-KR-		Low Friction Resistance Polyoxymethylene Composition	DOW SILICONES CORPORATION	03/26/2015	10-2016-7027388	
PCT	SOUTH KOREA					

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			Large Diameter Semiconductor Wafer For Integration With Power Device Manufacturing	DOW SILICONES		
DC11943-KR-						
PCT	SOUTH KOREA	Technology	CORPORATION	07/29/2015 10-2014-7005000	10-2017-0041223	
		Large Diameter Semiconductor Wafer For Integration With Power Device Manufacturing	DOW SILICONES			
DC11943-TW-						
NP	Taiwan	Technology	CORPORATION	07/29/2015 104124497	2201611098	
		METHOD FOR MANUFACTURING SIC WAFER FIT FOR INTEGRATION WITH POWER DEVICE	DOW SILICONES			
DC11943-US-	United States Of DIV	MANUFACTURING TECHNOLOGY	CORPORATION	03/04/2016 15/061959	20160189956	06/19/2018 10002760
		METHOD FOR MANUFACTURING SIC WAFER FIT FOR INTEGRATION WITH POWER DEVICE	DOW SILICONES			
DC11943-US-	United States Of NP	MANUFACTURING TECHNOLOGY	CORPORATION	12/29/2014 14/585101	2016-0032486	03/08/2016 9279192
DC11948-CN-			DOW SILICONES			
PCT	China	Pentachlorodisilane	CORPORATION	05/19/2016 201680028698.5	107614749	
DC11948-EP-	European Procedure		DOW SILICONES			
EPT	(Patents)	Pentachlorodisilane	CORPORATION	05/19/2016 16726733.5	3298177	
DC11948-JP-			DOW SILICONES			
PCT	Japan	Pentachlorodisilane	CORPORATION	05/19/2016 2017-559637		
DC11948-KR-			DOW SILICONES			
PCT	SOUTH KOREA	Pentachlorodisilane	CORPORATION	05/19/2016 10-2017-7035370	10-2018-0005221	
DC11948-TW-			DOW SILICONES			
NP	Taiwan	Pentachlorodisilane	CORPORATION	05/20/2016 105115713	201704244	
DC11948-US-	United States Of PCT	Pentachlorodisilane	DOW SILICONES	05/19/2016 15/558726	20180076025	
DC11950-CN-			DOW SILICONES			
PCT	China	Aminohydridodisilanes	CORPORATION	05/15/2017 PCT/US17/032619		
DC11950-JP-			DOW SILICONES			
PCT	Japan	Aminohydridodisilanes	CORPORATION	05/15/2017 PCT/US17/032619		
DC11950-KR-			DOW SILICONES			
PCT	SOUTH KOREA	Aminohydridodisilanes	CORPORATION	05/15/2017 PCT/US17/032619		
DC11950-TW-			DOW SILICONES			
NP	Taiwan	Aminohydridodisilanes	CORPORATION	05/16/2017 106116176	201806960	
DC11950-WO-	International Procedure	Aminohydridodisilanes Silicon Precursor, Method Of Forming A Layer Using The Same And Method Of Fabricating A	DOW SILICONES CORPORATION	05/15/2017 PCT/US17/032619	WO/2017/200908	
DC11983-KR-			DOW SILICONES			
NP	SOUTH KOREA	Semiconductor Device Using The Same Silicon Precursor, Method Of Forming A Layer Using The Same And Method Of Fabricating A	CORPORATION	04/16/2014 2014-0045575		
		Semiconductor Device Using The Same Silicon Precursor, Method Of Forming A Layer Using The Same And Method Of Fabricating A	DOW SILICONES			
DC11983-KR-						
NP[2]	SOUTH KOREA	Using The Same Silicon Precursor, Method Of Forming A Layer Using The Same And Method Of Fabricating A	CORPORATION	04/15/2015 2015-0053180	10-2015-0120306	
		Semiconductor Device Using The Same Silicon Precursor, Method Of Forming A Layer Using The Same And Method Of Fabricating A	DOW SILICONES			
DC11983-US-	United States Of DIV	Semiconductor Device Using The Same Silicon Precursor, Method Of Forming A Layer Using The Same And Method Of Fabricating A	CORPORATION	07/29/2016 15/223685	20160336328	02/20/2018 9899392
		Semiconductor Device Using The Same Multi-phase Silicone Acrylic Hybrid Visco- Elastic Compositions	DOW SILICONES			
DC11983-US-	United States Of NP	Multi-phase Silicone Acrylic Hybrid Visco- Elastic Compositions	CORPORATION	01/22/2015 14/602671	20150303060	
DC11984-CN-			DOW SILICONES			
PCT	China	And Methods Of Making Same	CORPORATION	02/05/2016 201680017558.8		

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DC11984-EP-EPT	European Procedure (Patents)	Multi-phase Silicone Acrylic Hybrid Visco-Elastic Compositions And Methods Of Making Same	DOW SILICONES CORPORATION	02/05/2016 16749621.5	3256504
DC11984-JP-PCT	Japan	Multi-phase Silicone Acrylic Hybrid Visco-Elastic Compositions And Methods Of Making Same	DOW SILICONES CORPORATION	02/05/2016 2017-540800	
DC11984-KR-PCT	SOUTH KOREA	Making Same Multi-phase Silicone Acrylic Hybrid Visco-Elastic Compositions And Methods Of	DOW SILICONES CORPORATION	02/05/2016 10-2017-7024922	10-2017-0115582
DC11984-US-PCT	United States Of America	And Methods Of Making Same Furnace for Seeded Sublimation of Wide Band Gap Crystals	DOW SILICONES CORPORATION	02/05/2016 15/545133	20180002583
DC11995-CN-PCT	China	Furnace for Seeded Sublimation of Wide Band Gap Crystals	DOW SILICONES CORPORATION	01/29/2016 201680008678.1	107223168
DC11995-EP-EPT	European Procedure (Patents)	Sublimation of Wide Band Gap Crystals Furnace for Seeded Sublimation of Wide Band Gap Crystals Furnace for Seeded	DOW SILICONES CORPORATION	01/29/2016 16707276.8	
DC11995-JP-PCT	Japan	Sublimation of Wide Band Gap Crystals Furnace for Seeded Sublimation of Wide Band Gap Crystals Furnace for Seeded	DOW SILICONES CORPORATION	01/29/2016 PCT/US16/015773	
DC11995-TW-NP	Taiwan	Sublimation of Wide Band Gap Crystals Furnace for Seeded Sublimation of Wide Band Gap Crystals Furnace for Seeded	DOW SILICONES CORPORATION	02/03/2016 105103469	201638371
DC11995-US-PCT	United States Of America	Sublimation of Wide Band Gap Crystals Sulfur-Containing Polyorganosiloxane Compositions And Related Aspects Sulfur-Containing	DOW SILICONES CORPORATION	01/29/2016 15/548082	20180002828
DC12001-CN-PCT	China	Polyorganosiloxane Compositions And Related Aspects Sulfur-Containing	DOW SILICONES CORPORATION	11/06/2015 201580070450.0	107109067
DC12001-EP-EPT	European Procedure (Patents)	Polyorganosiloxane Compositions And Related Aspects Sulfur-Containing	DOW SILICONES CORPORATION	11/06/2015 15858244.5	3218424
DC12001-JP-PCT	Japan	Polyorganosiloxane Compositions And Related Aspects Sulfur-Containing	DOW SILICONES CORPORATION	11/06/2015 2017-525409	2018-505917
DC12001-KR-PCT	SOUTH KOREA	Polyorganosiloxane Compositions And Related Aspects Sulfur-Containing	DOW SILICONES CORPORATION	11/06/2015 10-2017-7015760	10-2017-0083105
DC12001-TW-NP	Taiwan	Polyorganosiloxane Compositions And Related Aspects Sulfur-Containing	DOW SILICONES CORPORATION	10/23/2015 104134832	201631043
DC12001-US-PCT	United States Of America	Polyorganosiloxane Compositions And Related Aspects	DOW SILICONES CORPORATION	11/06/2015 15/518332	20170306150
DC15010-CN-PCT	China	Synthesis of Disilanylamines through Transamination	DOW SILICONES CORPORATION	12/16/2016 201680072355.9	
DC15010-JP-PCT	Japan	Synthesis of Disilanylamines through Transamination	DOW SILICONES CORPORATION	12/16/2016 2018-530829	
DC15010-KR-PCT	SOUTH KOREA	Synthesis of Disilanylamines through Transamination SYNTHESIS OF DISILANYLAMINES AND	DOW SILICONES CORPORATION	12/16/2016 10-2018-7018306	
DC15010-TW-NP	Taiwan	POLYSILANYLAMIN DOW SILICONES ES	DOW SILICONES CORPORATION	12/16/2016 105141894	201733908
DC15010-US-PCT	United States Of America	Synthesis of Disilanylamines through Transamination	DOW SILICONES CORPORATION	12/16/2016 15/779653	US-2018-0258107-A1
DC16009-WO-PCT	International Procedure	POLYMER COMPOSITION	DOW SILICONES CORPORATION	06/02/2017 PCT/IB17/000848	WO/2017/208081
DC16017-JP-NP	Japan	Grease composition, mechanical article and starter overrunning clutches	DOW SILICONES CORPORATION	03/11/2016 2016-047995	2017-160373

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DC16043-TW- NP DC16043-WO- PCT	Taiwan International Procedure	TRICHLORODISILAN E E METHOD OF European Procedure (Patents)	DOW SILICONES CORPORATION DOW SILICONES CORPORATION MAKING ALUMINUM FREE NEOPENTASILANE COPORATION METHOD OF MAKING ALUMINUM FREE NEOPENTASILANE COPORATION CHLORODISILAZANE DOW SILICONES S CHLORODISILAZANE DOW SILICONES S SIH-FREE VINYLDISILANES SIH-FREE VINYLDISILANES Thermoplastic Silicon NP[2] Malaysia	09/26/2017 106133001 09/21/2017 PCT/US17/052609	201813927 WO/2018/052609
DC16044-US- NP DC16054-TW- NP DC16054-WO- PCT DC16061-TW- NP DC16061-WO- PCT DC4525-MY- NP[2]	United States Of America Taiwan International Procedure	CHLORODISILAZANE DOW SILICONES S CHLORODISILAZANE DOW SILICONES S SIH-FREE VINYLDISILANES SIH-FREE VINYLDISILANES Thermoplastic Silicon Elastomers Method for Producing Hydrogenated Silicon Oxycarbide Films	DOW SILICONES COPORATION DOW SILICONES COPORATION DOW SILICONES COPORATION DOW SILICONES COPORATION DOW SILICONES COPORATION DOW SILICONES COPORATION	06/11/2018 16/004802 09/27/2017 106133216 09/21/2017 PCT/US17/52644 09/19/2017 106132149 09/15/2017 PCT/US17/051710	201817908 WO/2018/063907 201829305 WO/2018/057411
DC4648-JP- DIV	Japan	Having Low Dielectric Constant Method for Producing Hydrogenated Silicon Oxycarbide Films	DOW SILICONES COPORATION	10/26/2009 2009245328	2010028130 12/09/2011 4881422
DC4648-KR- NP	SOUTH KOREA	Having Low Dielectric Constant Method for Producing Hydrogenated Silicon Oxycarbide Films	DOW SILICONES COPORATION	05/27/1999 99/19173	10/11/2004 0453612
DC4648-TW- NP	Taiwan	Having Low Dielectric Constant Thermoplastic Silicone	DOW SILICONES COPORATION	05/13/1999 088107766	491910 06/21/2002 491910
DC4686-DE- EPA	Germany	Vulcanizates Prepared by Condensation Cure Thermoplastic Silicone	DOW SILICONES COPORATION	09/16/1999 99118344.3	0994151 03/29/2006 69930571.3
DC4686-FR- EPA	France	Vulcanizates Prepared by Condensation Cure Thermoplastic Silicone	DOW SILICONES COPORATION	09/16/1999 99118344.3	0994151 03/29/2006 0994151
DC4686-GB- EPA	United Kingdom	Vulcanizates Prepared by Condensation Cure Thermoplastic Silicone	DOW SILICONES COPORATION	09/16/1999 99118344.3	0994151 03/29/2006 0994151
DC4686-JP- NP	Japan	Vulcanizates Prepared by Condensation Cure Thermoplastic Silicone	DOW SILICONES COPORATION	10/07/1999 287053/99	109696/00 04/08/2011 4717976
DC4686-US- NP	United States Of America	Vulcanizates Prepared by Condensation Cure Fire Resistant	DOW SILICONES COPORATION	10/07/1998 09/167337	11/28/2000 6153691
DC4737-CN- PCT	China	Thermoplastic Silicone Vulcanizates Fire Resistant	DOW SILICONES COPORATION	01/31/2000 00803417.6	01/14/2004 00803417.6
DC4737-DE- EPT	Germany	Thermoplastic Silicone Vulcanizates Fire Resistant	DOW SILICONES COPORATION	01/31/2000 00910031.4	1153079 08/25/2004 60013252.8
DC4737-US- CNT	United States Of America	Thermoplastic Silicone Vulcanizates Pressure Sensitive Adhesive Compositions	DOW SILICONES COPORATION	06/13/2001 09/880480	2002-0055567 08/13/2002 6433049
DC4749-US- NP	United States Of America	for Transdermal Drug Delivery Devices	DOW SILICONES COPORATION	02/06/1999 09/245687	01/08/2002 6337086
DC4844-CN- PCT	China	Thermoplastic Silicone Elastomers Formed From Nylon Resins	DOW SILICONES COPORATION	03/21/2001 01807264.X	03/23/2005 01807264.X
DC4844-DE- EPT	Germany	Elastomers Formed From Nylon Resins	DOW SILICONES COPORATION	03/21/2001 01920590.5	09/01/2004 60105278.1
DC4844-KR- PCT	SOUTH KOREA	Thermoplastic Silicone Elastomers Formed From Nylon Resins	DOW SILICONES COPORATION	03/21/2001 2002/7012809	04/23/2007 712388
DC4844-US- CIP	United States Of America	Elastomers Formed From Nylon Resins	DOW SILICONES COPORATION	10/26/2001 10/015155	03/30/2004 6713569
DC4844-US- NP	United States Of America	Thermoplastic Silicone Elastomers Formed From Nylon Resins	DOW SILICONES COPORATION	03/27/2000 09/535556	03/26/2002 6362287
DC4891-DE- EPT	Germany	Elastomers Formed From Polyester Resins	DOW SILICONES COPORATION	12/03/2001 01999611.5	1354003 09/29/2004 60106086.5
DC4891-US- NP	United States Of America	Thermoplastic Silicone Elastomers Formed From Polyester Resins	DOW SILICONES COPORATION	12/04/2000 09/728920	2002-0103308 07/09/2002 6417293

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DC4912-US-NP	United States Of America	Polyolefin Thermoplastic Silicone Elastomers Employing Radical Cure	DOW SILICONES CORPORATION	04/30/2001 09/843906	11/12/2002 6479580
DC4913-US-NP	United States Of America	Thermoplastic Silicone Elastomers Employing Radical Cure	DOW SILICONES CORPORATION	05/01/2001 09/845971	10/15/2002 6465552
DC4962-CN-PCT	China	Elastomers from Compatibilized Polyester Resins Thermoplastic Silicone	DOW SILICONES CORPORATION	10/15/2002 02820615.0	1571820 04/19/2006 02820615.0
DC4962-DE-EPT	Germany	Elastomers from Compatibilized Polyester Resins Thermoplastic Silicone	DOW SILICONES CORPORATION	10/15/2002 02802140.0	1444298 10/07/2009 60233958.8
DC4962-US-NP	United States Of America	Elastomers from Compatibilized Polyester Resins Thermoplastic	DOW SILICONES CORPORATION	10/19/2001 10/043776	05/27/2003 6569958
DC4967-BR-PCT	Brazil	Polyurethane-Silicone Elastomers Thermoplastic	DOW SILICONES CORPORATION	10/22/2002 PI0213015-7	09/04/2012 PI0213015-7
DC4967-CA-PCT	Canada	Polyurethane-Silicone Elastomers Thermoplastic	DOW SILICONES CORPORATION	10/22/2002 2464455	01/04/2011 2464455
DC4967-CN-PCT	China	Polyurethane-Silicone Elastomers Thermoplastic	DOW SILICONES CORPORATION	10/22/2002 02820341.0	03/22/2006 02820341.0
DC4967-DE-EPT	Germany	Polyurethane-Silicone Elastomers Thermoplastic	DOW SILICONES CORPORATION	10/22/2002 02791189.0	1440122 09/12/2007 60222454.3
DC4967-JP-PCT	Japan	Polyurethane-Silicone Elastomers Thermoplastic	DOW SILICONES CORPORATION	10/22/2002 2003-538266	08/03/2012 5052738
DC4967-KR-PCT	SOUTH KOREA	Polyurethane-Silicone Elastomers Thermoplastic	DOW SILICONES CORPORATION	10/22/2002 10-2004-7005954	06/30/2010 0968355
DC4967-US-NP	United States Of America	Polyurethane-Silicone Elastomers Polyamide Based	DOW SILICONES CORPORATION	10/23/2002 10/278532	20030109623 07/06/2004 6759487
DC5026-US-NP	United States Of America	Thermoplastic silicone Elastomers Method For Producing	DOW SILICONES CORPORATION	07/18/2002 10/199345	2004-0014888 06/01/2004 6743868
DC5108-CN-PCT	China	Hydrogenated Silicon-Oxycarbide Films Method For Producing	DOW SILICONES CORPORATION	01/26/2004 200480005345.0	1754252 09/03/2008 200480005345.0
DC5108-JP-PCT	Japan	Hydrogenated Silicon-Oxycarbide Films Method For Producing	DOW SILICONES CORPORATION	01/26/2004 2006-503062	2006519496 12/09/2011 4881153
DC5108-KR-PCT	SOUTH KOREA	Hydrogenated Silicon-Oxycarbide Films Method For Producing	DOW SILICONES CORPORATION	01/26/2004 10-2005-7015852	05/31/2011 101039242
DC5108-TW-NP	Taiwan	Hydrogenated Silicon-Oxycarbide Films Method For Producing	DOW SILICONES CORPORATION	01/27/2004 093101750	200420750 07/21/2012 I368670
DC5108-US-PCT	United States Of America	Hydrogenated Silicon-Oxycarbide Films	DOW SILICONES CORPORATION	01/26/2004 10/543672	200600148252 03/13/2007 7189664
DC5183-CN-PCT	China	Method for Adhering Silicone Gels to Plastics	DOW SILICONES CORPORATION	09/30/2004 200480033420.4	1878577 11/03/2010 200480033420.4
DC5183-DE-EPT	Germany	Method for Adhering Silicone Gels to Plastics	DOW SILICONES CORPORATION	09/30/2004 04785363.5	1684814 10/22/2014 6020040460397
DC5183-FR-EPT	France	Method for Adhering Silicone Gels to Plastics	DOW SILICONES CORPORATION	09/30/2004 04785363.5	1684814 10/22/2014 1684814
DC5183-GB-EPT	United Kingdom	Method for Adhering Silicone Gels to Plastics	DOW SILICONES CORPORATION	09/30/2004 04785363.5	1684814 10/22/2014 1684814
DC5183-US-PCT	United States Of America	Method for Adhering Silicone Gels to Plastics	DOW SILICONES CORPORATION	09/30/2004 10/577032	20070042108 01/24/2012 8101042
PN26-CA-PCT	Canada	ANTIFRICTION COATING	DOW SILICONES CORPORATION	05/11/2001 2408683	08/03/2010 2408683
PN26-CN-PCT	China	COATING ANTIFRICTION	DOW SILICONES CORPORATION	05/11/2001 01809317.5	1429256A 10/21/2005 01809317.5
PN26-DE-EPT	Germany	COATING ANTIFRICTION	DOW SILICONES CORPORATION	05/11/2001 01943369.7	1280863 09/13/2006 60123038.8
PN26-ES-EPT	Spain	COATING ANTIFRICTION	DOW SILICONES CORPORATION	05/11/2001 01943369.7	1280863 09/13/2006 1280863
PN26-FR-EPT	France	COATING ANTIFRICTION	DOW SILICONES CORPORATION	05/11/2001 01943369.7	1280863 09/13/2006 1280863
PN26-GB-EPT	United Kingdom	COATING	DOW SILICONES CORPORATION	05/11/2001 01943369.7	1280863 09/13/2006 1280863

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PN26-IT-EPT	Italy	ANTIFRICTION COATING	DOW SILICONES CORPORATION	05/11/2001	01943369.7	1280863	09/13/2006	1280863
PN26-JP-PCT	Japan	COATING ANTIFRICTION	DOW SILICONES CORPORATION	05/11/2001	2001-582447		07/22/2011	4786853
PN26-KR-PCT	SOUTH KOREA	COATING ANTIFRICTION United States Of ANTIFRICTION	DOW SILICONES CORPORATION	05/11/2001	10-2002-7015121	793623	01/04/2008	793623
PN26-US-PCT	America	COATING ANTI CORROSION Procedure	DOW SILICONES CORPORATION	05/11/2001	10/275721	20040127625	11/21/2006	7138184
PN28-EP-EPT (Patents)		TOP COAT COMPOSITION ANTI CORROSION	DOW SILICONES CORPORATION	04/23/2002	02766637.9	1397443		
PN28-KR-PCT	SOUTH KOREA	COMPOSITION ANTI CORROSION United States Of TOP COAT	DOW SILICONES CORPORATION	04/23/2002	10-2003-7014260	10-955588	04/23/2010	10-955588
PN28-US-PCT	America	COMPOSITION Solar Cells and	DOW SILICONES CORPORATION	04/23/2002	10/475763	20040137238	12/18/2007	7309528
SN138-CN-PCT	China	Encapsulation Thereof Solar Cells and	DOW SILICONES CORPORATION	07/02/2004	200480019362.X	1816916	11/17/2010	200480019362X
SN138-DE-EPT	Germany European	Encapsulation Thereof	DOW SILICONES CORPORATION	07/02/2004	04741014.7	1644989	10/19/2011	602004034918.6
SN138-EP-EPT (Patents)		Solar Cells and Encapsulation Thereof	DOW SILICONES CORPORATION	07/02/2004	04741014.7	1644989	10/19/2011	1644989
SN138-ES-EPT	Spain	Solar Cells and Encapsulation Thereof	DOW SILICONES CORPORATION	07/02/2004	04741014.7	1644989	10/19/2011	1644989
SN138-FR-EPT	France	Solar Cells and Encapsulation Thereof	DOW SILICONES CORPORATION	07/02/2004	04741014.7	1644989	10/19/2011	1644989
SN138-GB-EPT	United Kingdom	Solar Cells and Encapsulation Thereof	DOW SILICONES CORPORATION	07/02/2004	04741014.7	1644989	10/19/2011	1644989
SN138-IT-EPT	Italy	Encapsulation Thereof Solar Cells and	DOW SILICONES CORPORATION	07/02/2004	04741014.7	1644989	10/19/2011	1644989
SN138-KR-DIV	SOUTH KOREA	Encapsulation Thereof Solar Cells and	DOW SILICONES CORPORATION	07/02/2004	20127003252		06/17/2014	1410709
SN138-KR-PCT	SOUTH KOREA	Encapsulation Thereof	DOW SILICONES CORPORATION	07/02/2004	20067000411		06/12/2012	1157407
SN138-US-CNT	America	United States Of Solar Cells and Encapsulation Thereof	DOW SILICONES CORPORATION	12/30/2011	13/341120	20120186631	09/30/2014	8847064
SN138-US-PCT	America	United States Of Solar Cells and Encapsulation Thereof	DOW SILICONES CORPORATION	07/02/2004	10/563677	20060207646	09/30/2014	8847063